





245NQ015/R-1 SCHOTTKY RECTIFIER



Features

- 125°C T_J operation(V_R<5V)
- Unique high power, Half-Pak module
- **Optimized for OR-ing applications**
- High purity, high temperature epoxy encapsulation for enhanced
- mechanical strength and moisture resistance
- Ultra low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Base plate: Nickel plated; Terminals: Nickel plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



The top side is terminal, the bottom side is base plate.

Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- **Reverse battery protection**

Maximum Ratings(limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ \end{array}$	-	15(DC) 25(Working)	V
Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =70°C, rectangular wave form	240	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	3600	Α
Non-Repetitive Avalanche Energy	E _{AS}	T _J =25°C,I _{AS} =2A,L=4.5mH	9	mJ
Repetitive Avalanche Current	I _{AR}	Current decaying linearly to zero in 1 μ sec Frequency limited by T_J max. V_A =3 \times V_R typical	2	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*		@ 240A, Pulse, T _J = 25 °C	0.40	0.45	V
	V _{F1}	@ 480A, Pulse, T _J = 25 °C	0.51	0.55	V
	\/_	@ 240A, Pulse, T _J = 125 °C	0.31	0.34	V
	V _{F2}	@ 480A, Pulse, T _J = 125 °C	0.38	0.44	V
Reverse Current*	I _{R1}	@V _R = rated V _R T _J = 25 °C	22	80	mA
	I _{R2}	@V _R = rated V _R T _J = 100 °C	662	4000	mA
	I _{R3}	@V _R = 12V, T _J = 100 °C	590	3560	mA
	I _{R4}	@V _R = 5V, T _J = 100 °C	440	2160	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 \text{ °C}$ $f_{SIG} = 1MHz$	13200	15800	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $^{^*}$ Pulse width < 300 μ s, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification		Units
Junction Temperature	TJ	-	-55 to +125		°C
Storage Temperature	T _{stg}	-	-55 to +150		°C
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.25		°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.07		°C/W
Mounting Torque	Тм	Non-lubricated threads	Mounting Torque	23(min) 29(max)	- Kg-cm
			Terminal Torque	35(min) 46(max)	
Approximate Weight	wt	-	36		g
Case Style	PRM1-1				

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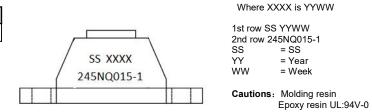
Ratings and Characteristics Curves

Figure 2 Figure1 Typical Reverse Characteristics Typical Forward Characteristics Instantaneous Reverse Current -IR (mA) 125°C 10³ 100°C Instantaneous Forward Current -I_F(A) 125°C 75°C 10² 75°C 10² 50°C 10¹ 25°C 25°C 9 15 Figure 3 Reverse Voltage -V_□(V) 10¹ Typical Junction Capacitance Junction Capacitance -C_T (PF) 100000 25°C 10000 10_{0.0} 0.2 0.3 0.4 0.5 0.6 0.7 Forward Voltage -V₋(V) 1000 L 40 Reverse Voltage -V_R(V)

Ordering Information

Device	Package	Shipping	
245NQ015-1	PRM1-1(Pb-Free)	27pcs/ box	

Marking Diagram



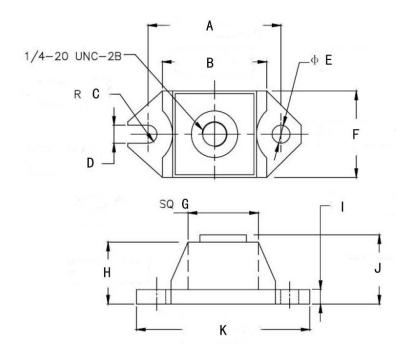
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Mechanical Dimensions PRM1-1 (Inches/Millimeters)



SYMBOL	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	29.35	30.95	1.155	1.219	
В	24.77	26.04	0.975	1.026	
С	1.79	2.19	0.070	0.087	
D	3.73	4.24	0.146	0.167	
Е	3.73	4.24	0.146	0.167	
F	18.42	19.69	0.725	0.775	
G	18.55	19.55	0.730	0.770	
Н	13.59	14.47	0.535	70.500	
I	3.05	3.90	0.120	0.154	
J	14.87	15.87	0.585	0.625	
K	38.61	39.62	1.520	1.560	







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